

# TRANSISTOR(PNP)

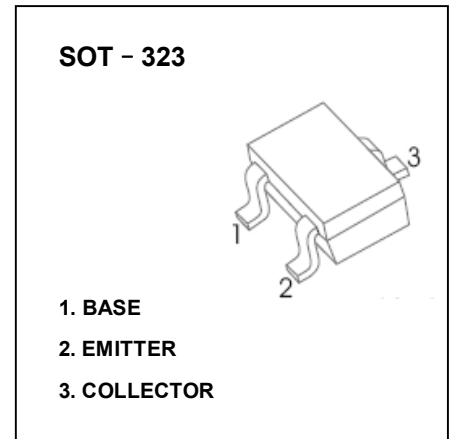
## FEATURES

- Small Surface Mount Package
- General Poupose for Amplification

**MARKING:K2G**

## MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CB0}$	Collector-Base Voltage	-80	V
$V_{CE0}$	Collector-Emitter Voltage	-80	V
$V_{EB0}$	Emitter-Base Voltage	-4	V
$I_C$	Collector Current	-500	mA
$P_C$	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	$^{\circ}\text{C/W}$
$T_j$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^{\circ}\text{C}$



## ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-4			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-80\text{V}, I_E=0$			-100	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-4\text{V}, I_C=0$			-0.5	nA
DC current gain	$h_{FE}$	$V_{CE}=-1\text{V}, I_C=-10\text{mA}$	50			
		$V_{CE}=-1\text{V}, I_C=-100\text{mA}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100\text{mA}, I_B=-10\text{mA}$			-0.25	V
Base-emitter voltage	$V_{BE}$	$V_{CE}=-1\text{V}, I_C=-100\text{mA}$			-1.2	V
Transition frequency	$f_T$	$V_{CE}=-1\text{V}, I_E=-100\text{mA}, f=100\text{MHz}$	50			MHz